

Electronic Supplementary Information (ESI) available:

A Developed Ullmann Reaction to III–V Semiconductor

Nanocrystals in Sealed Vacuum Tubes

Junli Wang and Qing Yang*

*Hefei National Laboratory for Physical Science at Microscale and Department of Chemistry,
University of Science and Technology of China (USTC), Hefei, Anhui 230026, P. R. China. Tel:
+86-551-3600243, Fax: +86-551-3606266, E-mail: qyoung@ustc.edu.cn.*

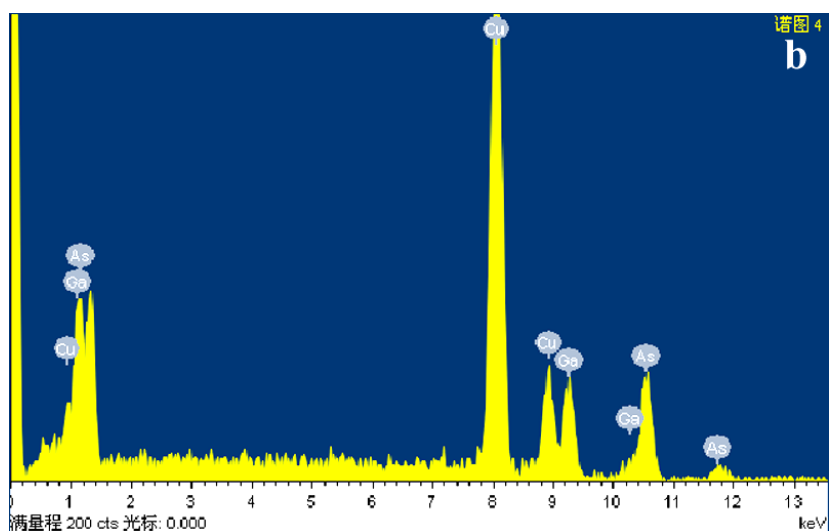
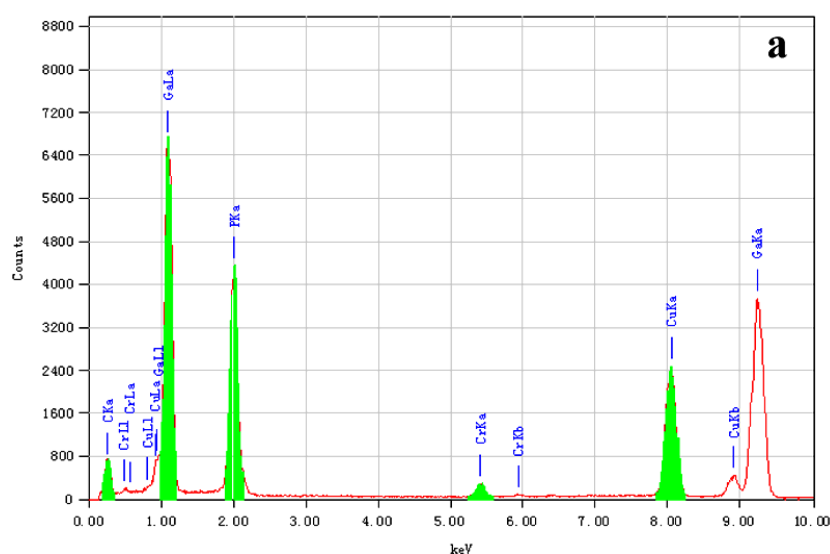


Figure 1S: Energy-dispersive X-ray spectroscopy (EDX) spectra of (a) the GaP products synthesized using 1 : 1.2 Ga : PPh₃ at 380 °C for 12 h; and (b) the GaAs products synthesized using 3 : 1 Ga : AsPh₃ at 360 °C for 24 h. The composition of the two products was close to 1:1 determined by EDX. The peaks of Cu and Cr are from the Cu grid of TEM.